

2N5550, 2N5551

Preferred Device

Amplifier Transistors

NPN Silicon

Features

- Pb-Free Packages are Available*
- Device Marking: Device Type, e.g., 2N5550, Date Code



ON Semiconductor®

<http://onsemi.com>

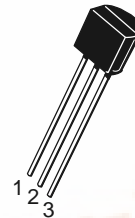
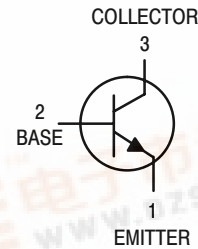
MAXIMUM RATINGS

Rating	Symbol	2N5550	2N5551	Unit
Collector – Emitter Voltage	V_{CEO}	140	160	Vdc
Collector – Base Voltage	V_{CBO}	160	180	Vdc
Emitter – Base Voltage	V_{EBO}	6.0		Vdc
Collector Current – Continuous	I_C	600		mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0		mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12		W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150		$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

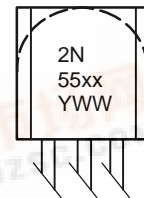
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$



TO-92
CASE 29
STYLE 1

MARKING DIAGRAM



55xx Specific Device Code
Y = Year
WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (Note 1) ($I_C = 1.0\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	140 160	– –	Vdc
Collector–Base Breakdown Voltage ($I_C = 100\text{ }\mu\text{A}$, $I_E = 0$)	$V_{(BR)CBO}$	160 180	– –	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10\text{ }\mu\text{A}$, $I_C = 0$)	$V_{(BR)EBO}$	6.0	–	Vdc
Collector Cutoff Current ($V_{CB} = 100\text{ Vdc}$, $I_E = 0$) ($V_{CB} = 120\text{ Vdc}$, $I_E = 0$) ($V_{CB} = 100\text{ Vdc}$, $I_E = 0$, $T_A = 100^\circ\text{C}$) ($V_{CB} = 120\text{ Vdc}$, $I_E = 0$, $T_A = 100^\circ\text{C}$)	I_{CBO}	– – – –	100 50 100 50	nAdc μAdc
Emitter Cutoff Current ($V_{EB} = 4.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	50	nAdc
ON CHARACTERISTICS (Note 1)				
DC Current Gain ($I_C = 1.0\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$) ($I_C = 10\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$) ($I_C = 50\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$)	h_{FE}	60 80 60 80 20 30	– – 250 250 – –	–
Collector–Emitter Saturation Voltage ($I_C = 10\text{ mA}$, $I_B = 1.0\text{ mA}$) ($I_C = 50\text{ mA}$, $I_B = 5.0\text{ mA}$)	$V_{CE(sat)}$	– – –	0.15 0.25 0.20	Vdc
Base–Emitter Saturation Voltage ($I_C = 10\text{ mA}$, $I_B = 1.0\text{ mA}$) ($I_C = 50\text{ mA}$, $I_B = 5.0\text{ mA}$)	$V_{BE(sat)}$	– – –	1.0 1.2 1.0	Vdc
SMALL–SIGNAL CHARACTERISTICS				
Current–Gain — Bandwidth Product ($I_C = 10\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	100	300	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	–	6.0	pF
Input Capacitance ($V_{EB} = 0.5\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{ibo}	– –	30 20	pF
Small–Signal Current Gain ($I_C = 1.0\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{fe}	50	200	–
Noise Figure ($I_C = 250\text{ }\mu\text{A}$, $V_{CE} = 5.0\text{ Vdc}$, $R_S = 1.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$)	NF	– –	10 8.0	dB

1. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

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ORDERING INFORMATION

Device	Package	Shipping [†]
2N5550	TO-92	5,000 Unit / Bulk
2N5550RLRA	TO-92	2,000 Tape & Reel
2N5550RLRP	TO-92	2,000 Tape & Ammo Box
2N5550RLRPG	TO-92 (Pb-Free)	2,000 Tape & Ammo Box
2N5551	TO-92	5,000 Unit / Bulk
2N5551G	TO-92 (Pb-Free)	5,000 Unit / Bulk
2N5551RL1	TO-92	2,000 Tape & Reel
2N5551RLRA	TO-92	2,000 Tape & Reel
2N5551RLRM	TO-92	2,000 Tape & Ammo Box
2N5551RLRP	TO-92	2,000 Tape & Ammo Box
2N5551ZL1	TO-92	2,000 Tape & Ammo Box

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

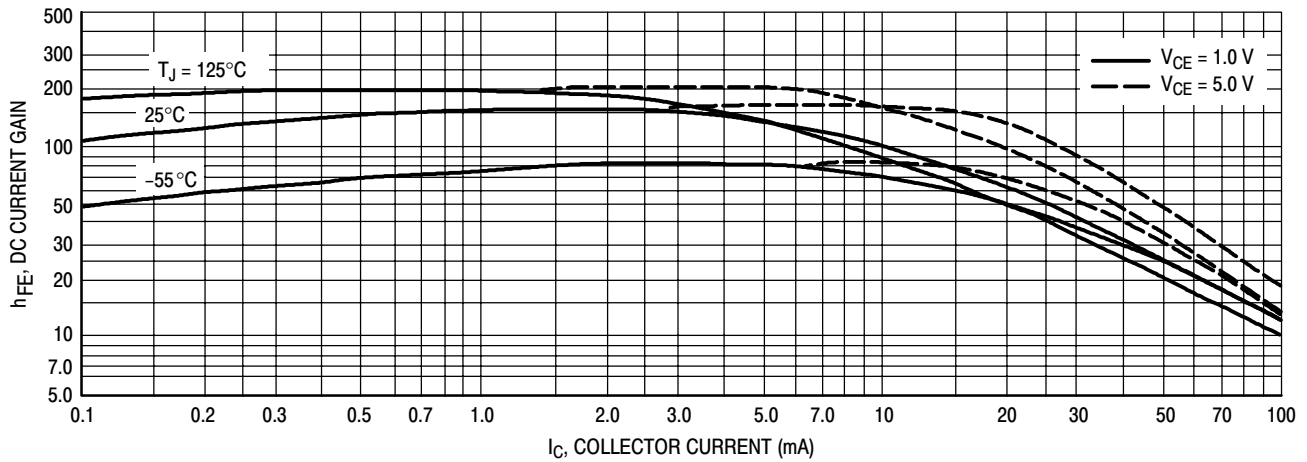


Figure 1. DC Current Gain

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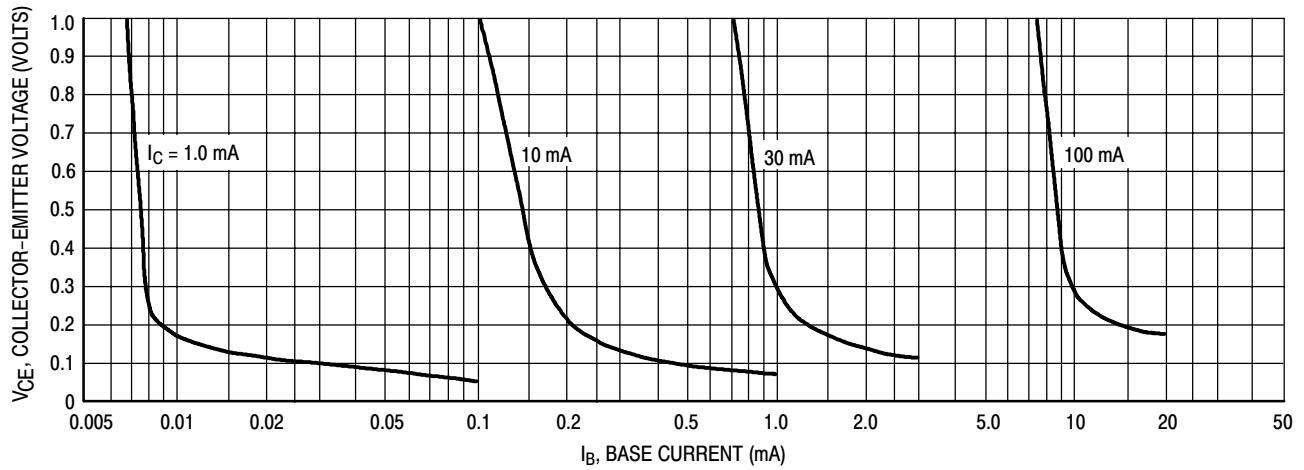


Figure 2. Collector Saturation Region

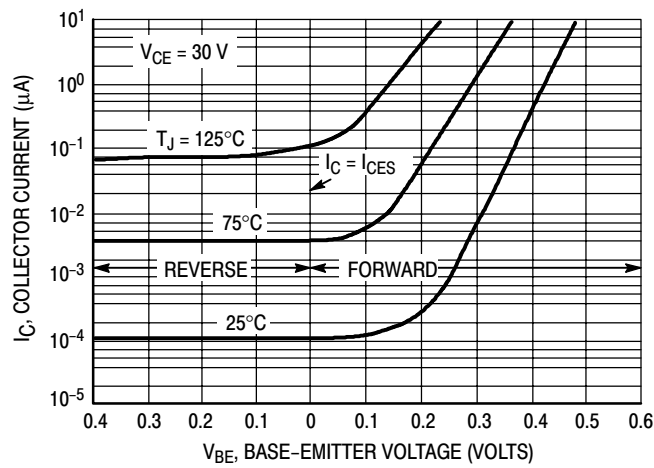


Figure 3. Collector Cut-Off Region

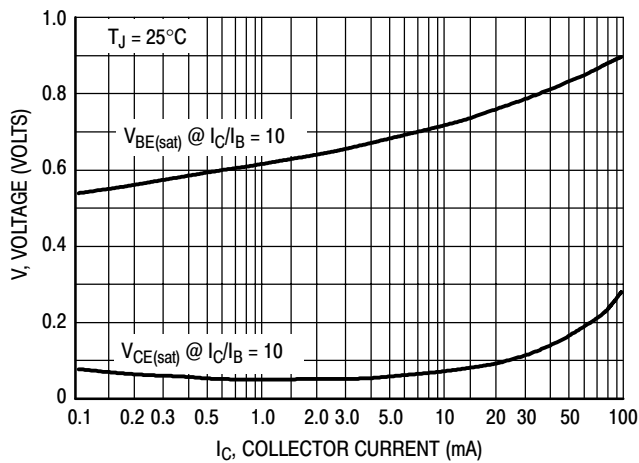


Figure 4. "On" Voltages

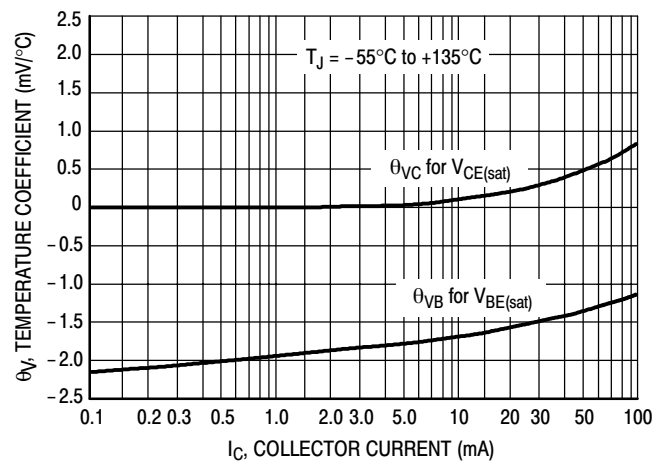
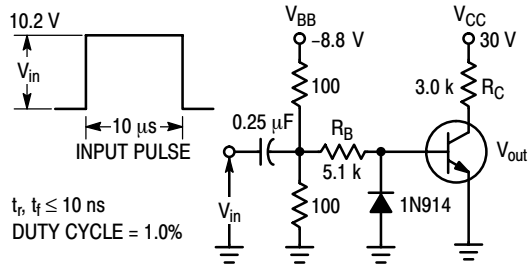


Figure 5. Temperature Coefficients

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Values Shown are for I_C @ 10 mA

Figure 6. Switching Time Test Circuit

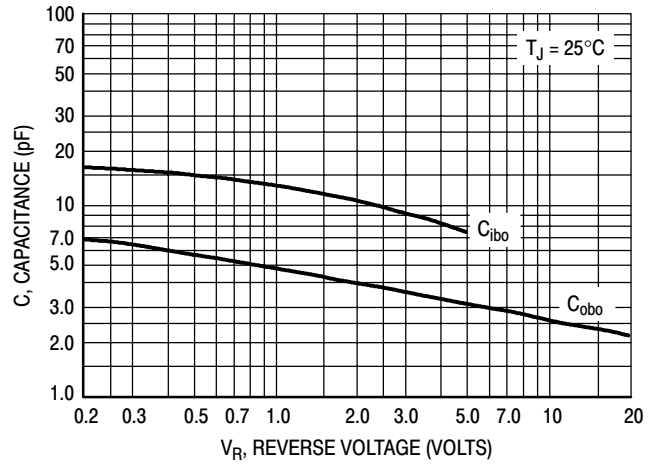


Figure 7. Capacitances

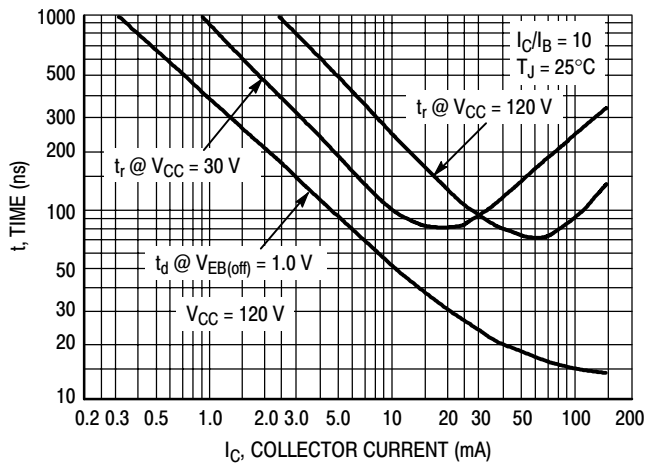


Figure 8. Turn-On Time

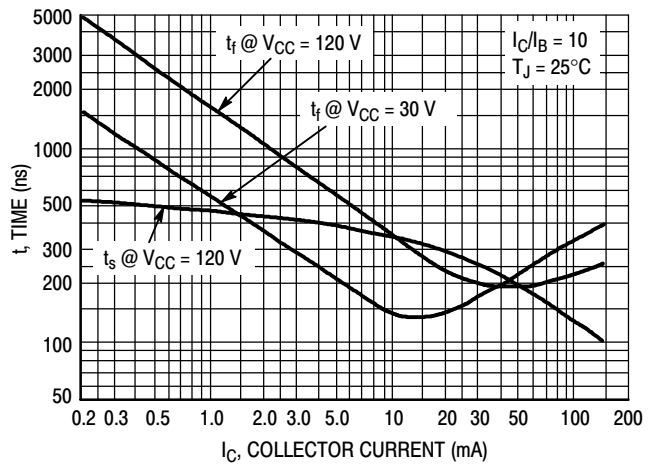
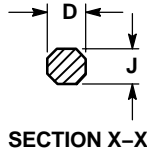
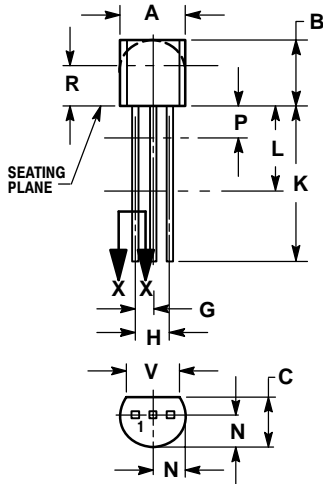


Figure 9. Turn-Off Time

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PACKAGE DIMENSIONS

TO-92
TO-226AA
CASE 29-11
ISSUE AL




NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 1:

1. PIN 1. EMITTER
2. BASE
3. COLLECTOR

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